TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K15F

High Speed Switching Applications Analog Switch Applications

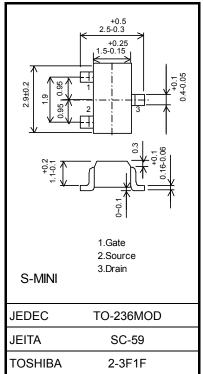
- Small package
- Low on resistance

TÖSHIBA

- : $R_{on} = 4.0 \Omega \text{ (max)} (@V_{GS} = 4 \text{ V})$
- : $R_{on} = 7.0 \Omega (max) (@V_{GS} = 2.5 V)$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	30	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	۱ _D	100	mA	
	Pulse	I _{DP}	200		
Drain power dissipation (Ta = 25° C)		PD	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature		T _{stg}	-55~150	°C	



Weight: 0.012 g (typ.)

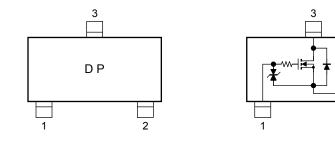
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Marking

Equivalent Circuit



Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Unit: mm

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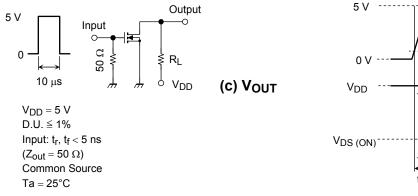
Electrical Characteristics (Ta = 25°C)

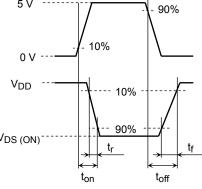
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 16~V,~V_{DS}=0$			±1	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	30	_	_	V
Drain cut-off curre	nt	I _{DSS}	$V_{DS} = 30 V, V_{GS} = 0$	_	_	1	μA
Gate threshold vol	tage	V _{th}	$V_{DS} = 3 V, I_D = 0.1 mA$	0.8	_	1.5	V
Forward transfer a	dmittance	Y _{fs}	$V_{DS} = 3 V, I_D = 10 mA$	25	_	_	mS
Drain-source ON resistance		R _{DS (ON)}	$I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$	_	2.2	4.0	Ω
			$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	4.0	7.0	
Input capacitance		C _{iss}	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	7.8	_	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	3.6	_	pF
Output capacitance		C _{oss}	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$		8.8		pF
Switching time	Turn-on time	t _{on}	V _{DD} = 5 V, I _D = 10 mA, V _{GS} = 0~5 V	_	50	_	ns
	Turn-off time	t _{off}			180	_	

Switching Time Test Circuit

(a) Test circuit

(b) V_{IN}





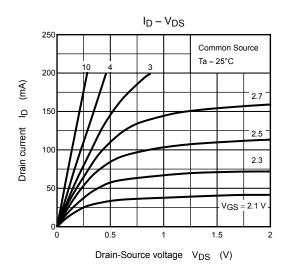
Precaution

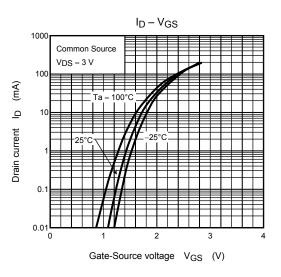
 V_{th} can be expressed as voltage between gate and source when low operating current value is I_D = 100 μA for this product. For normal switching operation, V_{GS} (on) requires higher voltage than V_{th} and V_{GS} (off) requires lower voltage than V_{th} .

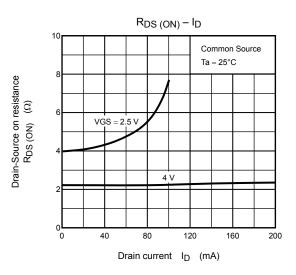
(relationship can be established as follows: V_{GS} (off) $< V_{th} < V_{GS}$ (on))

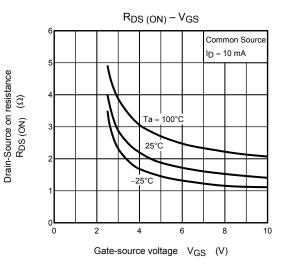
Please take this into consideration for using the device.

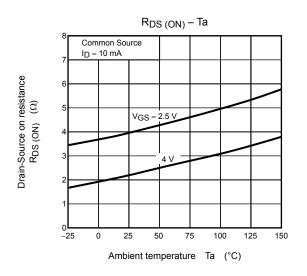


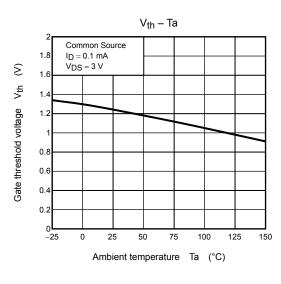




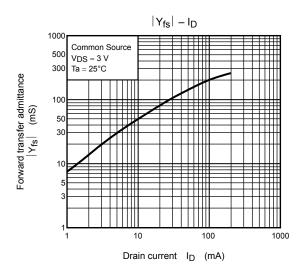


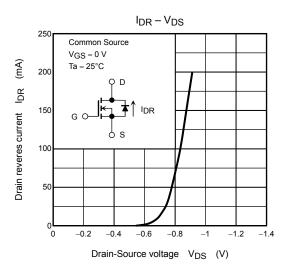


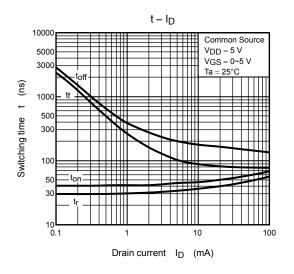


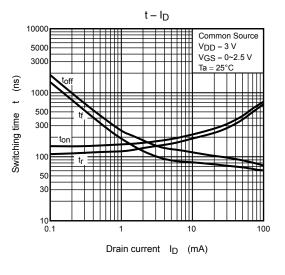


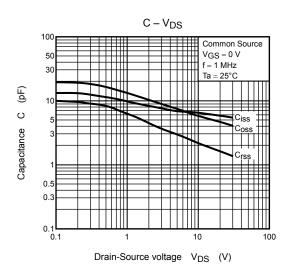


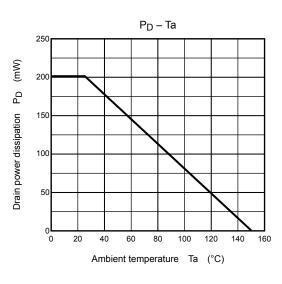














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TOSHIBA

20070701-EN GENERAL

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
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